



2N7000

Power MOSFET

N-CHANNEL ENHANCEMENT MODE

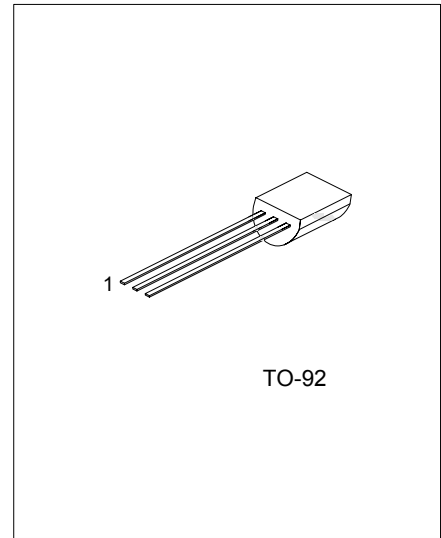
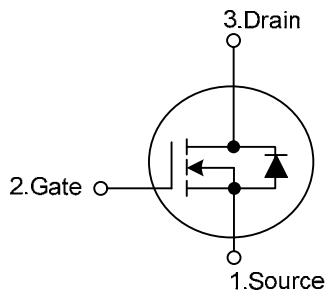
DESCRIPTION

The UTC **2N7000** has been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. It can be used in most applications requiring up to 400mA DC and can deliver pulsed currents up to 2A. The product is particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications

FEATURES

- *High density cell design for low $R_{DS(ON)}$
- *Voltage controlled small signal switch
- *Rugged and reliable
- *High saturation current capability

SYMBOL



*Pb-free plating product number:2N7000L

ORDERING INFORMATION

| Order Number | | Package | Pin Assignment | | | Packing |
|--------------|-------------------|---------|----------------|---|---|-----------|
| Normal | Lead Free Plating | | 1 | 2 | 3 | |
| 2N7000-T92-B | 2N7000L-T92-B | TO-92 | S | G | D | Tape Box |
| 2N7000-T92-K | 2N7000L-T92-K | TO-92 | S | G | D | Bulk |
| 2N7000-T92-R | 2N7000L-T92-R | TO-92 | S | G | D | Tape Reel |

Note: Pin Assignment: G: Gate D: Drain S: Source

| | |
|---|---|
| <p>2N7000L-T92-B</p> <p>(1)Packing Type (2)Package Type (3)Lead Plating</p> | <p>(1) B: Tape Box, K: Bulk, R: Tape Reel (2) T92: TO-92 (3) L: Lead Free Plating, Blank: Pb/Sn</p> |
|---|---|

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---|--------------------------|----------------------------------|------------|-------|
| Drain-Source Voltage | | V _{DSS} | 60 | V |
| Drain-Gate Voltage (R _{GS} ≤1MΩ) | | V _{DGR} | 60 | V |
| Gate -Source Voltage | Continuous | V _{GS} | ±20 | V |
| | Non Repetitive (tp<50μs) | | ±40 | V |
| Maximum Drain Current | Continuous | I _D | 115 | mA |
| | Pulsed | | 800 | mA |
| Maximum Power Dissipation | | P _D | 400 | mW |
| Derated above 25°C | | | 3.2 | mW/°C |
| Operating and Storage Temperature | | T _J ,T _{STG} | -55 ~ +150 | °C |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

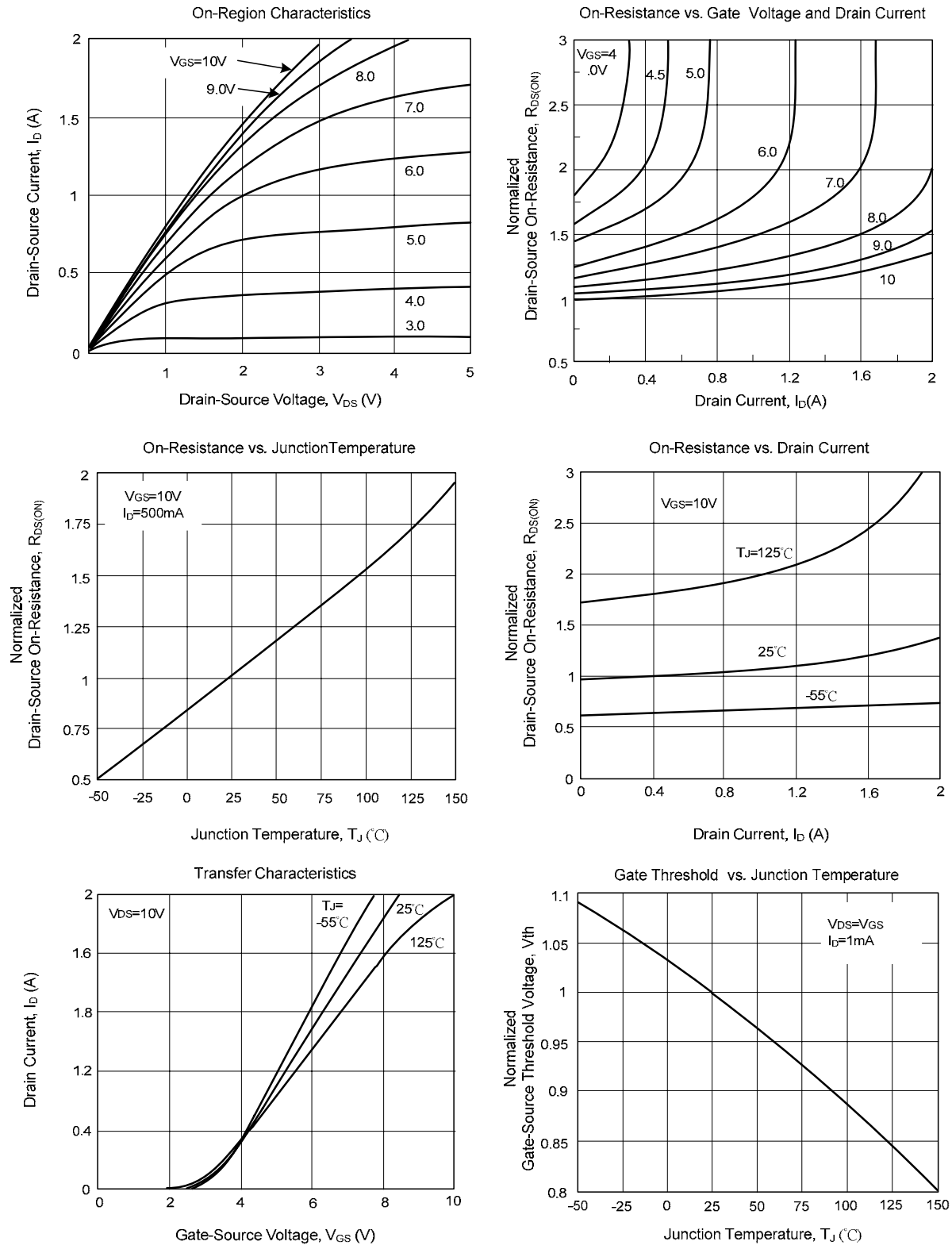
| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------|-----------------|---------|------|
| Junction-to-Ambient | θ _{JA} | 312.5 | °C/W |

■ ELECTRICAL CHARACTERISTICS (Ta =25°C, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---------------------|---|-----|------|------|------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =10 μA | 60 | | | V |
| Drain-Source Leakage Current | I _{DSS} | V _{DS} =60V, V _{GS} =0V T _J =125°C | | | 1 | μA |
| | | | | | 0.5 | mA |
| Gate-Body leakage, Forward | I _{GSSF} | V _{GS} =20V, V _{DS} =0V | | | 100 | nA |
| Gate-Body leakage Reverse | I _{GSSR} | V _{GS} =-20V, V _{DS} =0V | | | -100 | nA |
| ON CHARACTERISTICS (Note) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | V _{DS} =V _{GS} , I _D =250μA | 1 | 2.1 | 2.5 | V |
| Static Drain-Source On-Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =500mA T _J =100°C | | 1.2 | 7.5 | Ω |
| | | V _{GS} =5.0V, I _D =50mA T _J =100°C | | 1.7 | 13.5 | |
| | | | | 1.7 | 7.5 | |
| Drain-Source On-Voltage | V _{DS(ON)} | V _{GS} =10V, I _D =500mA | | 0.6 | 3.75 | V |
| | | V _{GS} =5.0V, I _D =50mA | | 0.09 | 1.5 | |
| On-State Drain Current | I _{D(ON)} | V _{GS} =10V, V _{DS} =2V _{DS(ON)} | 500 | 2700 | | mA |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | C _{ISS} | V _{DS} =25V, V _{GS} =0V, f=1.0MHz | | 20 | 50 | pF |
| Output Capacitance | C _{OSS} | | | 11 | 25 | pF |
| Reverse Transfer Capacitance | C _{RSS} | | | 4 | 5 | pF |
| Turn-On Time | t _{ON} | V _{DD} =30V, R _L =150Ω, I _D =200mA, V _{GS} =10V, R _{GEN} =25Ω | | | 20 | ns |
| Turn-Off Time | t _{OFF} | V _{DD} =30V, R _L =150Ω, I _D =200mA, V _{GS} =10V, R _{GEN} =25Ω | | | 20 | ns |
| DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS | | | | | | |
| Drain-Source Diode Forward Voltage | V _{SD} | V _{GS} =0V, I _S =115mA(Note) | | 0.88 | 1.5 | V |
| Maximum Continuous Drain-Source Diode Forward Current | I _S | | | | 115 | mA |
| Maximum Pulsed Drain-Source Diode Forward Current | I _{SM} | | | | 0.8 | A |

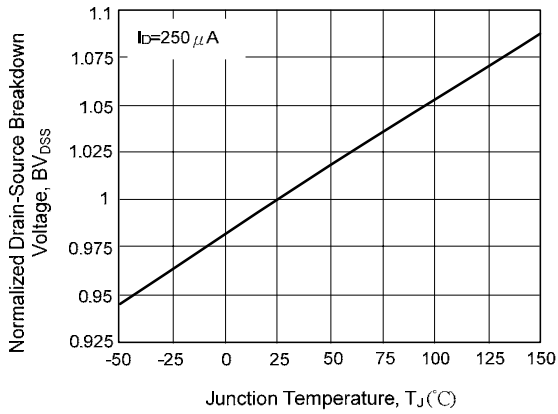
Note: Pulse Test: Pulse Width≤300μs, Duty Cycle≤2.0%

■ TYPICAL CHARACTERISTICS

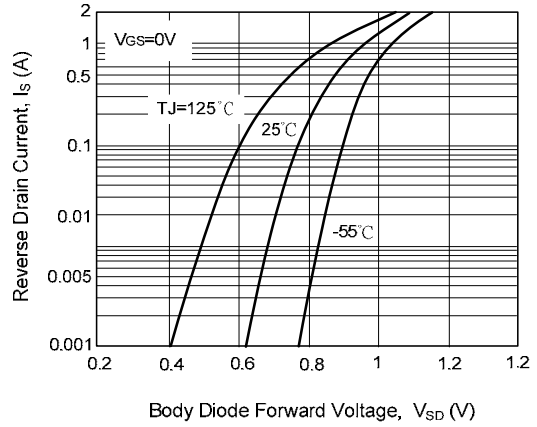


■ TYPICAL CHARACTERISTICS(Cont.)

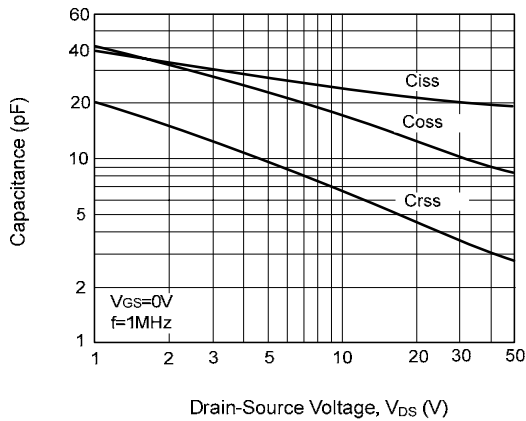
Breakdown Voltage vs. Junction Temperature



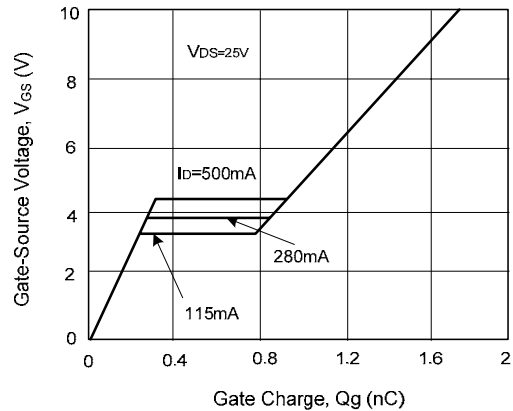
Reverse Drain Current vs. Body Diode Forward Voltage



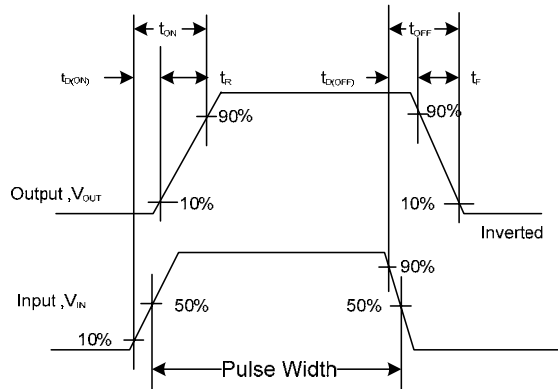
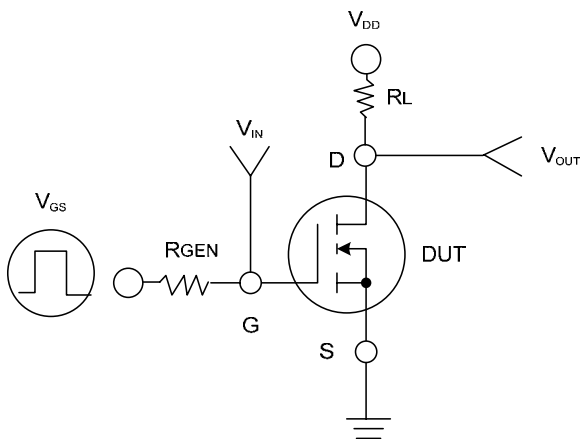
Capacitance Characteristics



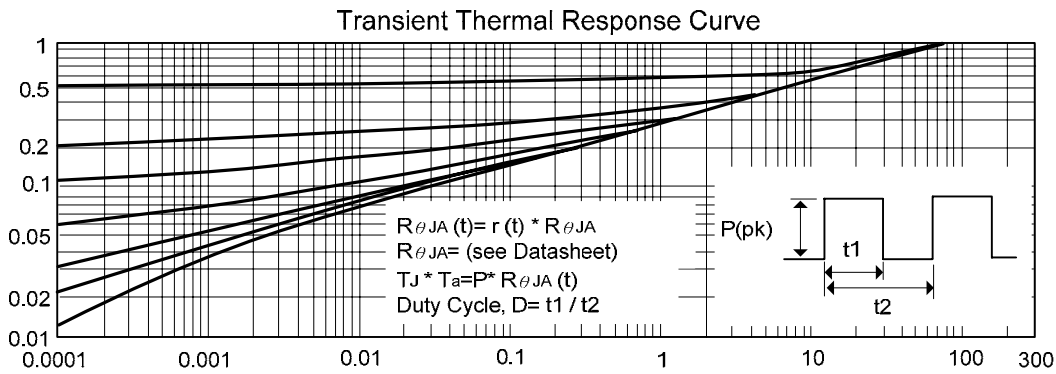
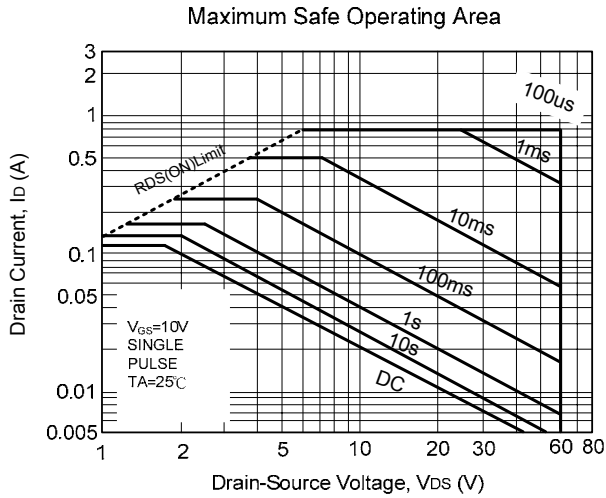
Gate Charge Characteristics



Switching Waveforms



■ TYPICAL CHARACTERISTICS(Cont.)



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